

TM026G04S

N+P-Channel Enhancement Mode Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

Product Summary

N Channel

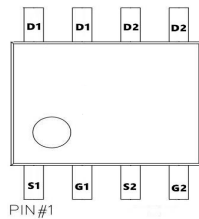
$V_{DS} = 40V, I_D = 7.3A$
 $R_{DS(ON)} = 26m\Omega (typ.) @ V_{GS} = 10V$

P Channel

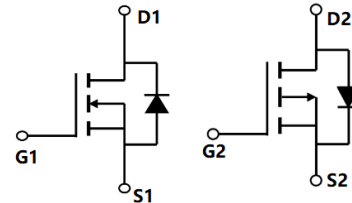
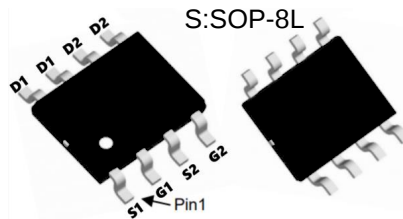
$V_{DS} = -40V, I_D = -6.1A$
 $R_{DS(ON)} = 56m\Omega (typ.) @ V_{GS} = -10V$

100% UIS Tested

100% R_g Tested



Marking: 7004



Absolute Maximum Ratings ($T_c = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating		Units
		N-Ch	P-Ch	
V_{DS}	Drain-Source Voltage	40	-40	V
V_{GS}	Gate-Source Voltage	± 20	± 20	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	7.3	-6.1	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	4.9	-3.8	A
I_{DM}	Pulsed Drain Current ²	26	-22	A
EAS	Single Pulse Avalanche Energy ³	16.2	39	mJ
I_{AS}	Avalanche Current	6.8	-6.8	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation ⁴	1.67	1.67	W
T_{STG}	Storage Temperature Range	-55 to 150	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	57		$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	30		$^\circ C/W$



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N-Channel Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	40	44	---	V
$\Delta BVDSS/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	---	0.034	---	V/ $^\circ\text{C}$
RDS(ON)	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=5A$	---	26	36	m Ω
		$V_{GS}=4.5V$, $I_D=4A$	---	36	49	
VGS(th)	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1.2	1.6	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4.56	---	mV/ $^\circ\text{C}$
IDSS	Drain-Source Leakage Current	$V_{DS}=32V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=32V$, $V_{GS}=0V$, $T_J=55^\circ\text{C}$	---	---	5	
IGSS	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
gfs	Forward Transconductance	$V_{DS}=5V$, $I_D=5A$	---	14	---	S
R _g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	2.6	---	Ω
Q _g	Total Gate Charge (4.5V)	$V_{DS}=20V$, $V_{GS}=4.5V$, $I_D=5A$	---	5.5	---	nC
Q _{gs}	Gate-Source Charge		---	1.25	---	
Q _{gd}	Gate-Drain Charge		---	2.5	---	
Td(on)	Turn-On Delay Time	$V_{DD}=20V$, $V_{GS}=10V$, $R_G=3.3\Omega$ $I_D=1A$	---	8.9	---	ns
T _r	Rise Time		---	2.2	---	
Td(off)	Turn-Off Delay Time		---	41	---	
T _f	Fall Time		---	2.7	---	
C _{iss}	Input Capacitance	$V_{DS}=15V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	593	---	pF
C _{oss}	Output Capacitance		---	76	---	
C _{rss}	Reverse Transfer Capacitance		---	56	---	
I _s	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	7.3	A
ISM	Pulsed Source Current ^{2,5}		---	---	23	A
VSD	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=1A$, $T_J=25^\circ\text{C}$	---	---	1.2	V

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3、The EAS data shows Max. rating . The test condition is $V_{DD}=25V$, $V_{GS}=10V$, $L=0.1\text{mH}$, $I_{AS}=10A$
- 4、The power dissipation is limited by 150°C junction temperature
- 5、The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

**TM026G04S****N+P-Channel Enhancement Mode Mosfet****P-Channel Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	-40	-44	---	V
$\Delta BVDSS/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=-1mA$	---	-0.018	---	V/ $^\circ\text{C}$
RDS(ON)	Static Drain-Source On-Resistance ²	$V_{GS}=-10V$, $I_D=-3A$	---	56	76	m Ω
		$V_{GS}=-4.5V$, $I_D=-2A$	---	76	85	
VGS(th)	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu A$	-1.0	-1.5	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	2.5	---	mV/ $^\circ\text{C}$
IDSS	Drain-Source Leakage Current	$V_{DS}=-40V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	-1	μA
		$V_{DS}=-40V$, $V_{GS}=0V$, $T_J=55^\circ\text{C}$	---	---	-5	
IGSS	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
gfs	Forward Transconductance	$V_{DS}=-5V$, $I_D=-3A$	---	5.8	---	S
Qg	Total Gate Charge (-4.5V)	$V_{DS}=-32V$, $V_{GS}=-4.5V$, $I_D=-3A$	---	6.4	---	nC
Qgs	Gate-Source Charge		---	2.1	---	
Qgd	Gate-Drain Charge		---	2.5	---	
Td(on)	Turn-On Delay Time	$V_{DD}=-20V$, $V_{GS}=-4.5V$, $R_G=3.3\Omega$, $I_D=-3A$	---	4.2	---	ns
Tr	Rise Time		---	23	---	
Td(off)	Turn-Off Delay Time		---	26.8	---	
Tf	Fall Time		---	20.6	---	
Ciss	Input Capacitance	$V_{DS}=-15V$, $V_{GS}=0V$, $f=1MHz$	---	620	---	pF
Coss	Output Capacitance		---	65	---	
Crss	Reverse Transfer Capacitance		---	53	---	
IS	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	-6.1	A
ISM	Pulsed Source Current ^{2,4}		---	---	-16.1	A
VSD	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=-1A$, $T_J=25^\circ\text{C}$	---	---	-1	V

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2、The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3、The power dissipation is limited by 150°C junction temperature
- 4、The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



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N-Channel Typical Characteristics

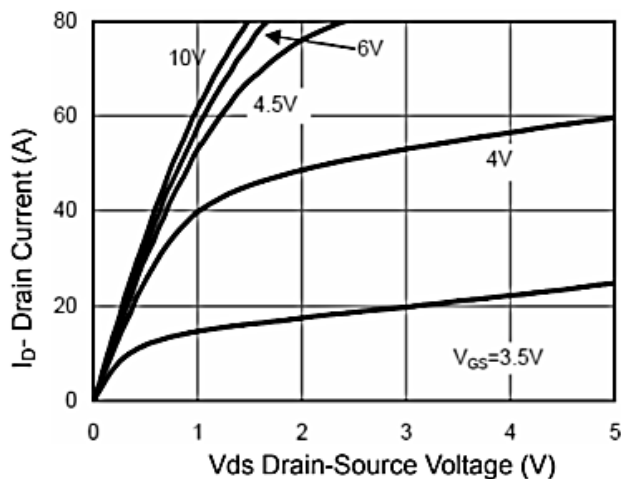


Figure 1 Output Characteristics

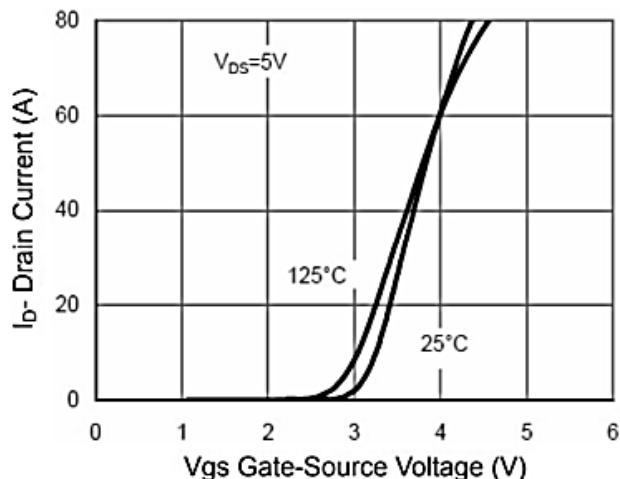


Figure 2 Transfer Characteristics

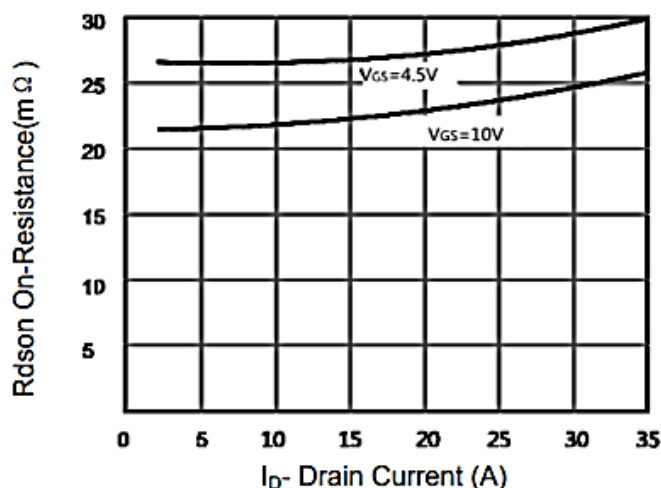
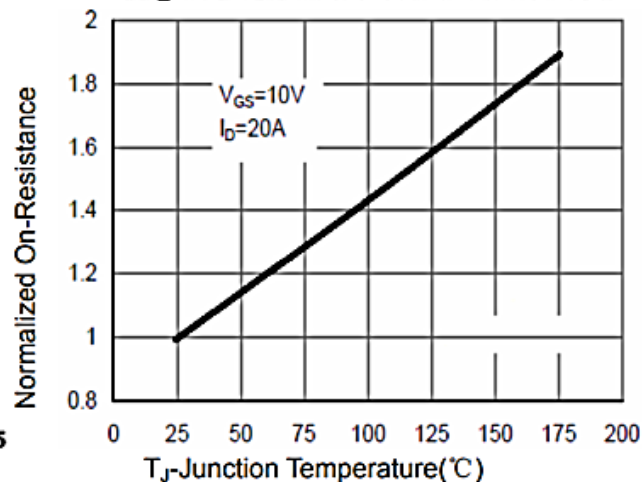
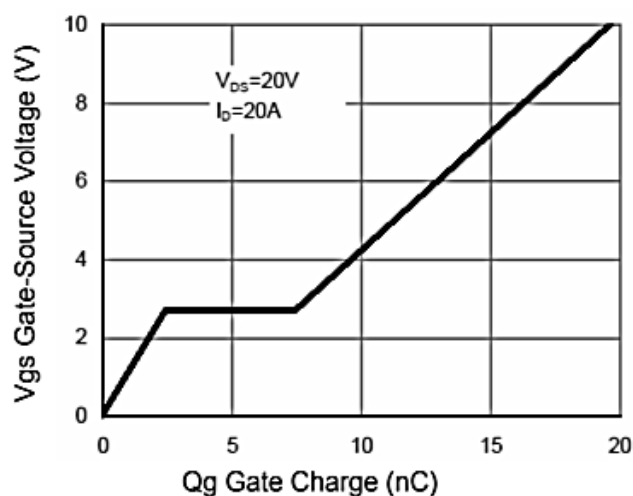
Figure 3 $R_{DS(on)}$ - Drain CurrentFigure 4 $R_{DS(on)}$ -Junction Temperature

Figure 5 Gate Charge

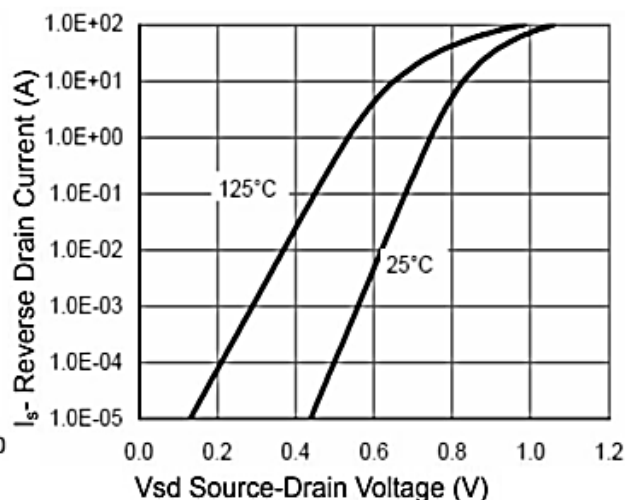


Figure 6 Source- Drain Diode Forward



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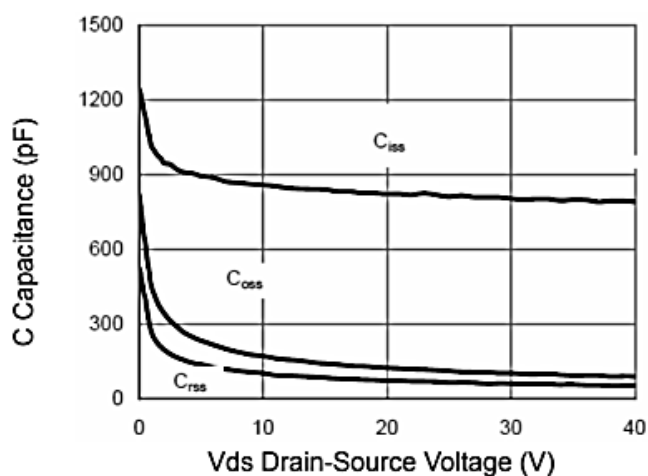


Figure 7 Capacitance vs Vds

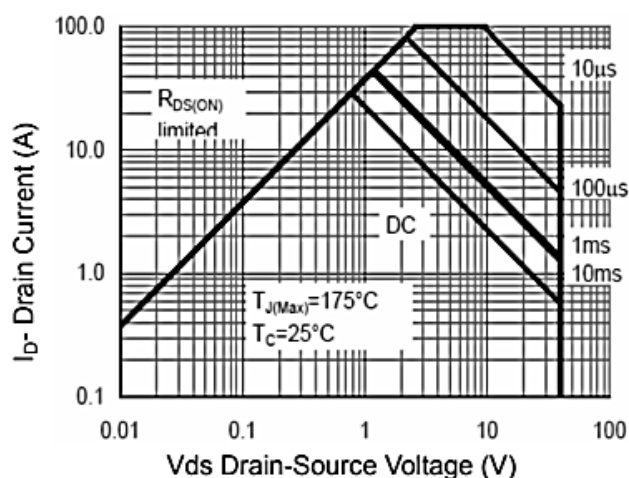


Figure 8 Safe Operation Area

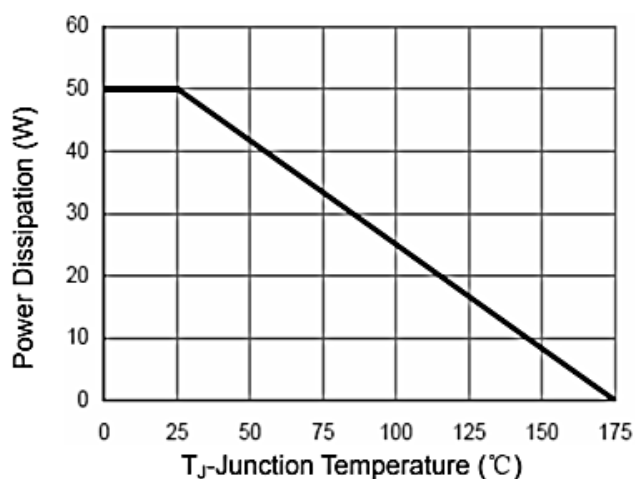


Figure 9 Power De-rating

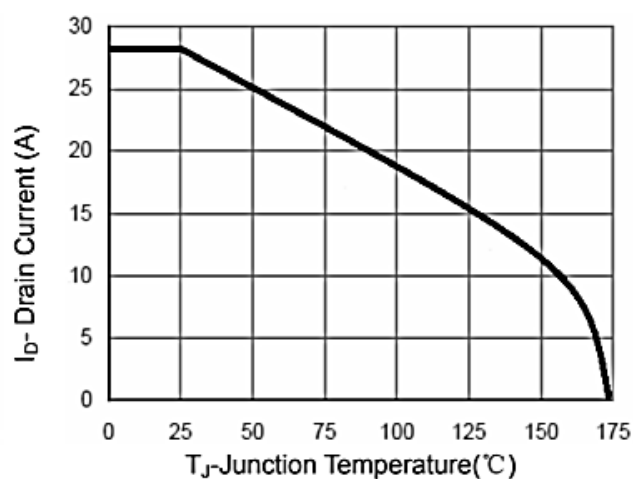


Figure 10 Id Current De-rating

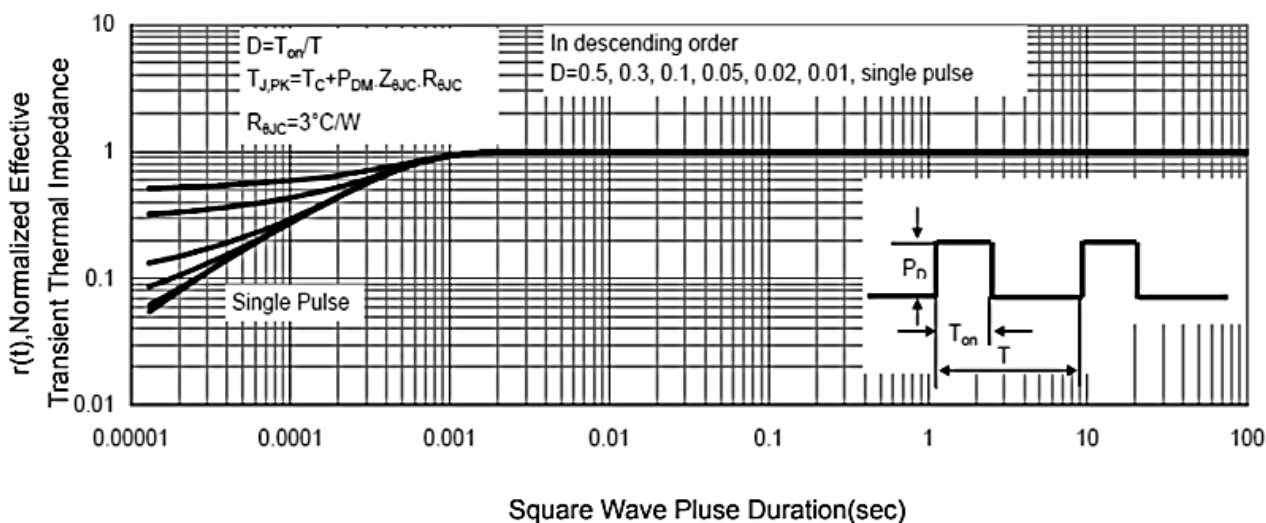


Figure 11 Normalized Maximum Transient Thermal Impedance



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P-Typical Characteristics

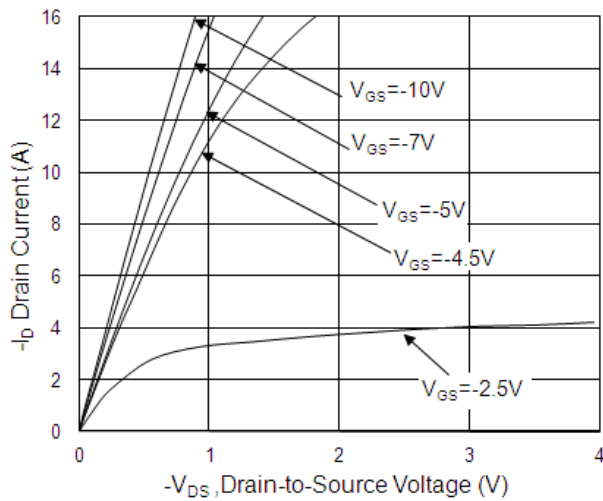


Fig.1 Typical Output Characteristics

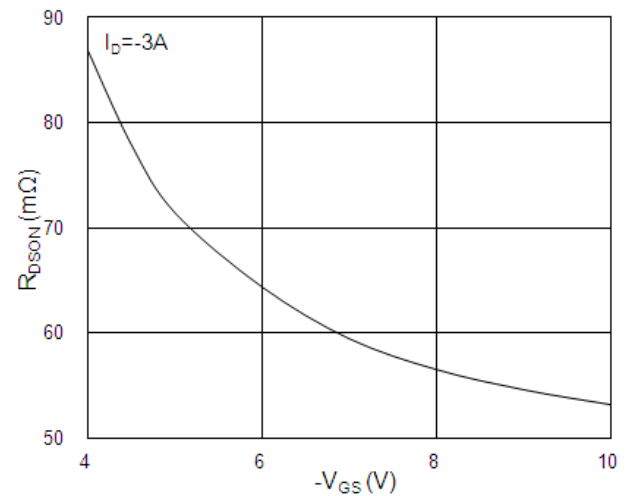


Fig.2 On-Resistance vs. G-S Voltage

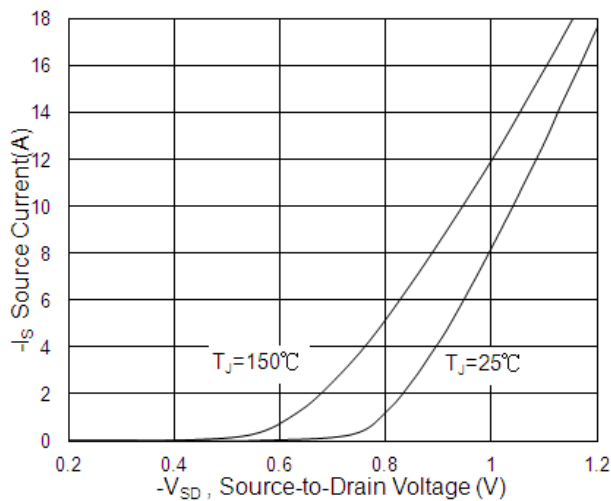


Fig.3 Forward Characteristics Of Reverse

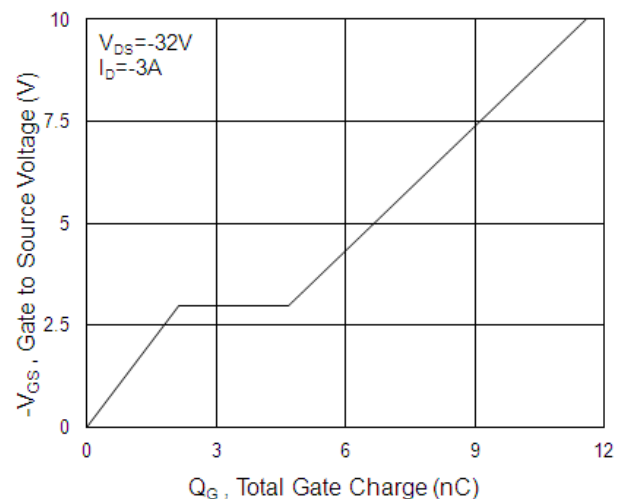
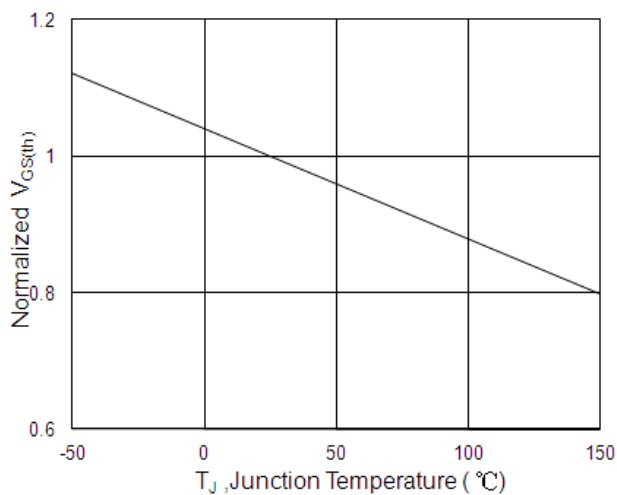
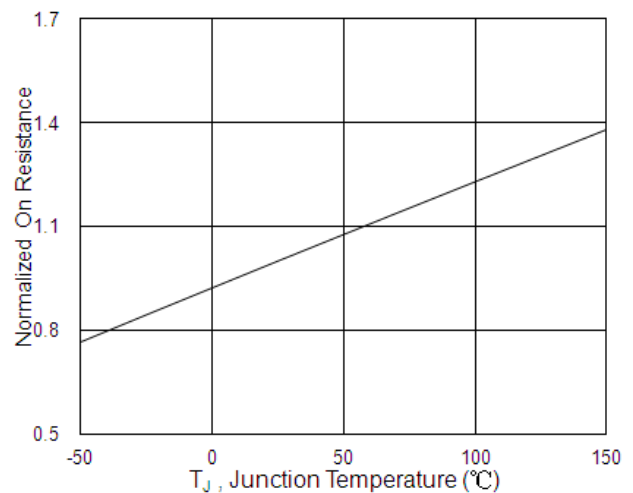


Fig.4 Gate-Charge Characteristics

Fig.5 Normalized $V_{GS(th)}$ vs. T_J Fig.6 Normalized $R_{DS(on)}$ vs. T_J



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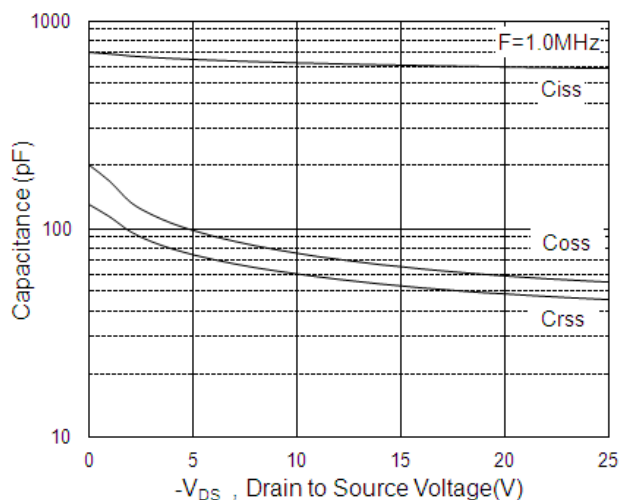


Fig.7 Capacitance

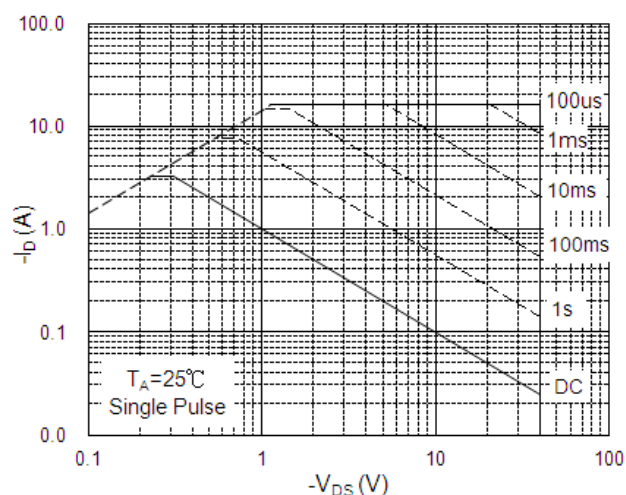


Fig.8 Safe Operating Area

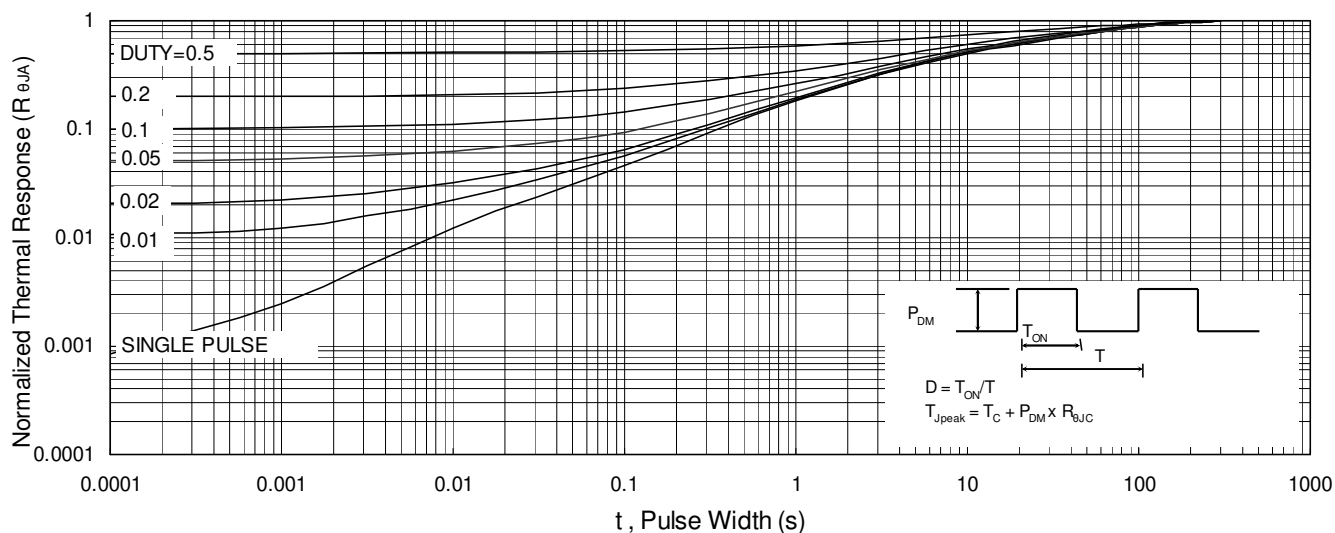


Fig.9 Normalized Maximum Transient Thermal Impedance

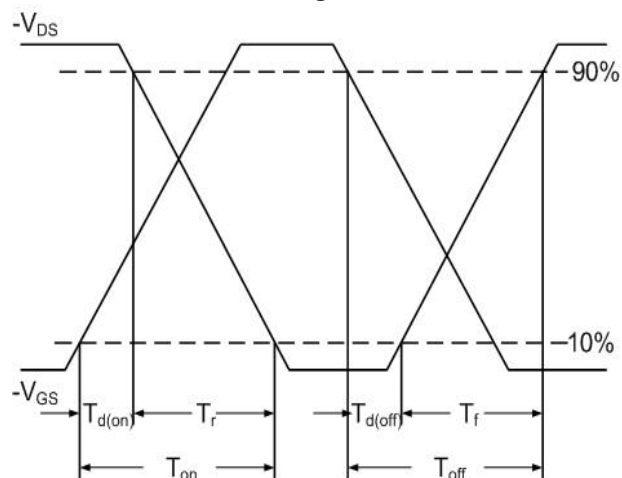


Fig.10 Switching Time Waveform

Data and specifications subject to change without notice.

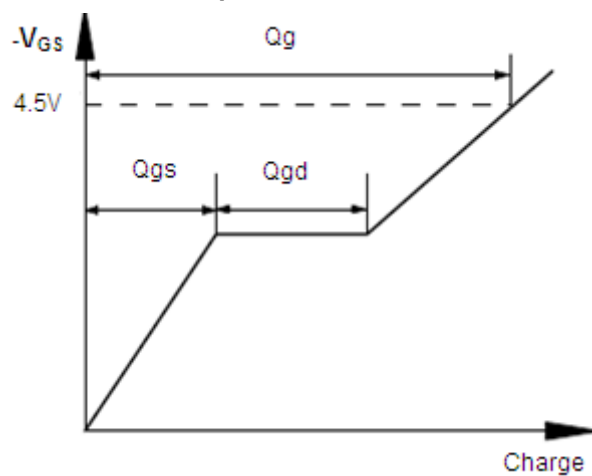
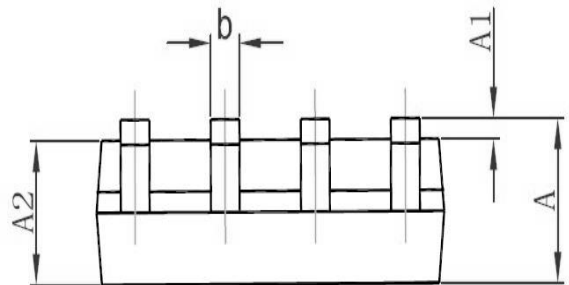
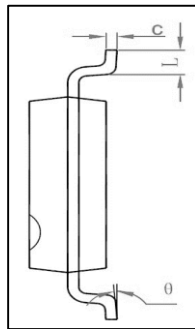
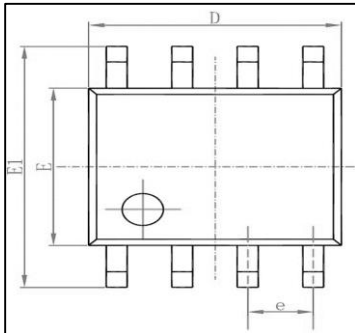
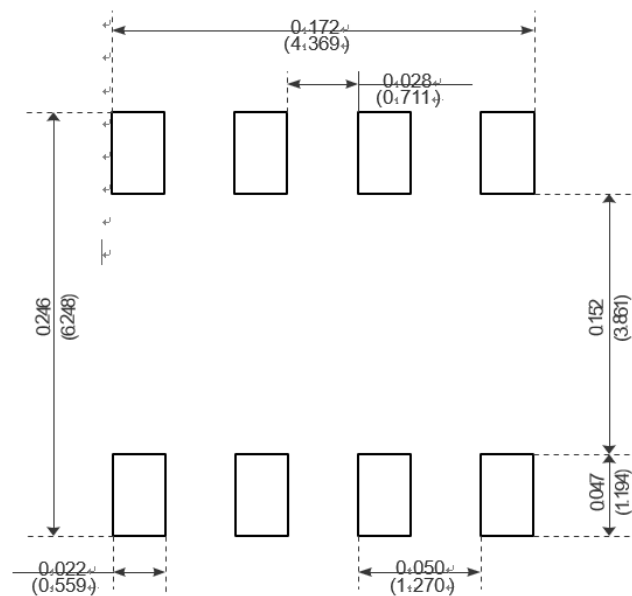


Fig.11 Gate Charge Waveform

Package Mechanical Data:SOP-8L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Recommended Minimum Pads